## RJK03F0DPA

Silicon N Channel Power MOS FET
REJ03G1934-0210 Power Switching

## Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
$\mathrm{R}_{\mathrm{DS}(\text { on })}=5.3 \mathrm{~m} \Omega$ typ. (at $\mathrm{V}_{\mathrm{GS}}=8 \mathrm{~V}$ )
- Pb-free
- Halogen-free


## Outline

RENESAS Package code: PWSN0008DC-A
(Package name: WPAK(2))


1,2,3 Source
4 Gate
5, 6, 7, 8 Drain

## Absolute Maximum Ratings

| Item | Symbol | Ratings | Unit |
| :---: | :---: | :---: | :---: |
| Drain to source voltage | $V_{\text {DSS }}$ | 30 | V |
| Gate to source voltage | $\mathrm{V}_{\text {GSS }}$ | $\pm 12$ | V |
| Drain current | $\mathrm{I}_{\mathrm{D}}$ | 30 | A |
| Drain peak current | $\mathrm{I}_{\mathrm{D} \text { (pulse) }}{ }^{\text {Note1 }}$ | 120 | A |
| Body-drain diode reverse drain current | $\mathrm{I}_{\mathrm{DR}}$ | 30 | A |
| Avalanche current | $\mathrm{I}_{\mathrm{AP}}{ }^{\text {Note } 2}$ | 12 | A |
| Avalanche energy | $\mathrm{EAR}^{\text {Note } 2}$ | 14.4 | mJ |
| Channel dissipation | Pch ${ }^{\text {Note3 }}$ | 30 | W |
| Channel to case thermal impedance | $\theta$ ch-c ${ }^{\text {Note3 }}$ | 4.17 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Channel temperature | Tch | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage temperature | Tstg | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |

Notes: 1. $\mathrm{PW} \leq 10 \mu \mathrm{~s}$, duty cycle $\leq 1 \%$
2. Value at $\mathrm{Tch}=25^{\circ} \mathrm{C}, \mathrm{Rg} \geq 50 \Omega$
3. $\mathrm{Tc}=25^{\circ} \mathrm{C}$

## Electrical Characteristics

$\left(\mathrm{Ta}=25^{\circ} \mathrm{C}\right)$

| Item | Symbol | Min | Typ | Max | Unit | Test Conditions |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Drain to source breakdown voltage | $\mathrm{V}_{\text {(BR) }}$ Dss | 30 | - | - | V | $\mathrm{I}_{\mathrm{D}}=10 \mathrm{~mA}, \mathrm{~V}_{\mathrm{GS}}=0$ |
| Gate to source leak current | $\mathrm{I}_{\text {gss }}$ | - | - | $\pm 0.1$ | $\mu \mathrm{A}$ | $\mathrm{V}_{\mathrm{GS}}= \pm 12 \mathrm{~V}, \mathrm{~V}_{\mathrm{DS}}=0$ |
| Zero gate voltage drain current | IDSs | - | - | 1 | $\mu \mathrm{A}$ | $\mathrm{V}_{\mathrm{DS}}=30 \mathrm{~V}, \mathrm{~V}_{\mathrm{GS}}=0$ |
| Gate to source cutoff voltage | $\mathrm{V}_{\mathrm{GS} \text { (off) }}$ | 1.2 | - | 2.5 | V | $\mathrm{V}_{\mathrm{DS}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=1 \mathrm{~mA}$ |
| Static drain to source on state resistance | $\mathrm{R}_{\mathrm{DS} \text { (on) }}$ | - | 5.3 | 6.4 | $\mathrm{m} \Omega$ | $\mathrm{I}_{\mathrm{D}}=15 \mathrm{~A}, \mathrm{~V}_{\mathrm{GS}}=8.0 \mathrm{~V}^{\text {Note4 }}$ |
|  | $\mathrm{R}_{\mathrm{DS} \text { (on) }}$ | - | 6.3 | 7.8 | $\mathrm{m} \Omega$ | $\mathrm{I}_{\mathrm{D}}=15 \mathrm{~A}, \mathrm{~V}_{\mathrm{GS}}=4.5 \mathrm{~V}^{\text {Note4 }}$ |
| Forward transfer admittance | $\left\|y_{\text {fs }}\right\|$ | - | 80 | - | S | $\mathrm{I}_{\mathrm{D}}=15 \mathrm{~A}, \mathrm{~V}_{\mathrm{DS}}=5 \mathrm{~V}^{\text {Note4 }}$ |
| Input capacitance | Ciss | - | 2150 | 3010 | pF | $\begin{aligned} & V_{\mathrm{DS}}=10 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{GS}}=0 \\ & \mathrm{f}=1 \mathrm{MHz} \end{aligned}$ |
| Output capacitance | Coss | - | 240 | - | pF |  |
| Reverse transfer capacitance | Crss | - | 140 | - | pF |  |
| Gate Resistance | Rg | - | 1.7 | 3.4 | $\Omega$ |  |
| Total gate charge | Qg | - | 15 | - | nC | $\begin{aligned} & \mathrm{V}_{\mathrm{DD}}=10 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{GS}}=4.5 \mathrm{~V} \\ & \mathrm{I}_{\mathrm{D}}=30 \mathrm{~A} \end{aligned}$ |
| Gate to source charge | Qgs | - | 6.1 | - | nC |  |
| Gate to drain charge | Qgd | - | 4.4 | - | nC |  |
| Turn-on delay time | $\mathrm{t}_{\mathrm{d}(\mathrm{O})}$ | - | 12.5 | - | ns | $\begin{aligned} & \mathrm{V}_{G S}=8 \mathrm{~V}, \mathrm{I}_{\mathrm{D}}=15 \mathrm{~A} \\ & \mathrm{~V}_{\mathrm{DD}} \cong 10 \mathrm{~V} \\ & \mathrm{R}_{\mathrm{L}}=0.67 \Omega \\ & \mathrm{Rg}^{2}=4.7 \Omega \end{aligned}$ |
| Rise time | $\mathrm{t}_{\mathrm{r}}$ | - | 4.8 | - | ns |  |
| Turn-off delay time | $\mathrm{t}_{\mathrm{d} \text { (off) }}$ | - | 43 | - | ns |  |
| Fall time | $\mathrm{t}_{\mathrm{f}}$ | - | 7.3 | - | ns |  |
| Body-drain diode forward voltage | $\mathrm{V}_{\mathrm{DF}}$ | - | 0.87 | 1.13 | V | $\mathrm{I}_{\mathrm{F}}=30 \mathrm{~A}, \mathrm{~V}_{\mathrm{GS}}=0^{\text {Note } 4}$ |
| Body-drain diode reverse recovery time | $\mathrm{t}_{\mathrm{rr}}$ | - | 16 | - | ns | $\begin{aligned} & \mathrm{I}_{\mathrm{F}}=30 \mathrm{~A}, \mathrm{~V}_{\mathrm{GS}}=0 \\ & \mathrm{di}_{\mathrm{F}} / \mathrm{dt}=100 \mathrm{~A} / \mu \mathrm{S} \end{aligned}$ |

Notes: 4. Pulse test

## Main Characteristics




Normalized Transient Thermal Impedance vs. Pulse Width


Avalanche Test Circuit


## Switching Time Test Circuit



Avalanche Waveform
$E_{A R}=\frac{1}{2} L \cdot I_{A P}{ }^{2} \cdot \frac{V_{D S S}}{V_{D S S}-V_{D D}}$


Switching Time Waveform


## Package Dimensions



## Ordering Information

| Part No. | Quantity | Shipping Container |
| :---: | :--- | :--- |
| RJK03F0DPA-00-J53 | 3000 pcs | Taping |

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